

BD675, BD675A, BD677, BD677, BD679A, BD681*

Preferred Device

Plastic Medium-Power Silicon NPN Darlington

This series of plastic, medium-power silicon NPN Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

Features

- Pb-Free Package is Available*
- High DC Current Gain:
 $h_{FE} = 750$ (Min) @ I_C
 $= 1.5$ and 2.0 Adc
- Monolithic Construction
- BD675, 675A, 677, 677A, 679, 679A, 681 are complementary with BD676, 676A, 678, 678A, 680, 680A, 682
- BD677, 677A, 679, 679A are equivalent to MJE 800, 801, 802, 803

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD675, A BD677, A BD679, A BD681	V_{CEO}	45 60 80 100	Vdc
Collector-Base Voltage BD675, A BD677, A BD679, A BD681	V_{CBO}	45 60 80 100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	4.0	Adc
Base Current	I_B	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	3.13	$^\circ\text{C/W}$

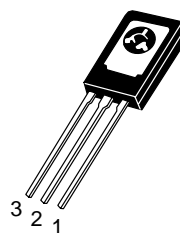
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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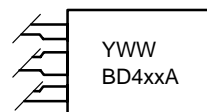
<http://onsemi.com>

**4.0 AMPERES
POWER TRANSISTORS
NPN SILICON
60, 80, 100 VOLTS
40 WATTS**



TO-225AA
CASE 77
STYLE 1

MARKING DIAGRAM



xx = 75, 77, 79, 81
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
BD675	TO-225AA	500 Units/Box
BD675A	TO-225AA	500 Units/Box
BD677	TO-225AA	500 Units/Rail
BD677A	TO-225AA	500 Units/Box
BD679	TO-225AA	500 Units/Box
BD679A	TO-225AA	500 Units/Box
BD679AG	TO-225AA (Pb-Free)	500 Units/Box
BD681	TO-225AA	500 Units/Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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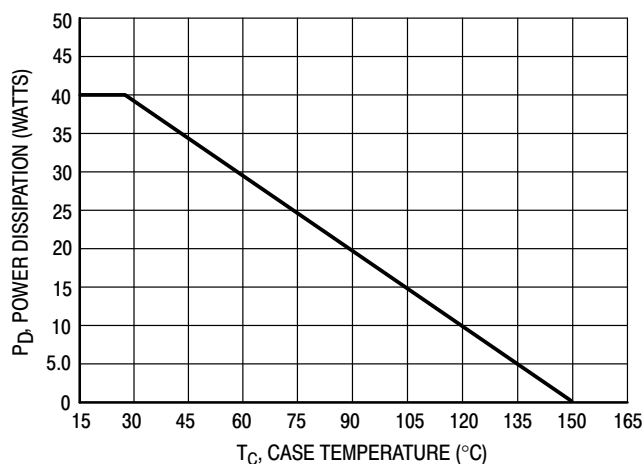


Figure 1. Power Temperature Derating

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage, (Note 1) (I _C = 50 mAdc, I _B = 0)	BV _{CEO}	45 60 80 100	– – – –	Vdc
Collector Cutoff Current (V _{CE} = Half Rated V _{CEO} , I _B = 0)	I _{CEO}	–	500	μAdc
Collector Cutoff Current (V _{CB} = Rated BV _{CEO} , I _E = 0) (V _{CB} = Rated BV _{CEO} , I _E = 0, T _C = 100°C)	I _{CBO}	– –	0.2 2.0	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	–	2.0	mAdc
ON CHARACTERISTICS				
DC Current Gain, (Note 1) (I _C = 1.5 Adc, V _{CE} = 3.0 Vdc) (I _C = 2.0 Adc, V _{CE} = 3.0 Vdc)	h _{FE}	750 750	– –	–
Collector–Emitter Saturation Voltage, (Note 1) (I _C = 1.5 Adc, I _B = 30 mAdc) (I _C = 2.0 Adc, I _B = 40 mAdc)	V _{CE(sat)}	– –	2.5 2.8	Vdc
Base–Emitter On Voltage, (Note 1) (I _C = 1.5 Adc, V _{CE} = 3.0 Vdc) (I _C = 2.0 Adc, V _{CE} = 3.0 Vdc)	V _{BE(on)}	– –	2.5 2.5	Vdc
DYNAMIC CHARACTERISTICS				
Small Signal Current Gain (I _C = 1.5 Adc, V _{CE} = 3.0 Vdc, f = 1.0 MHz)	h _{fe}	1.0	–	–

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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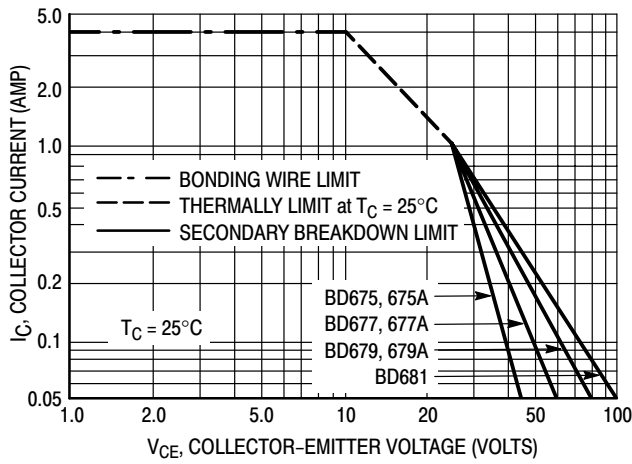


Figure 2. DC Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

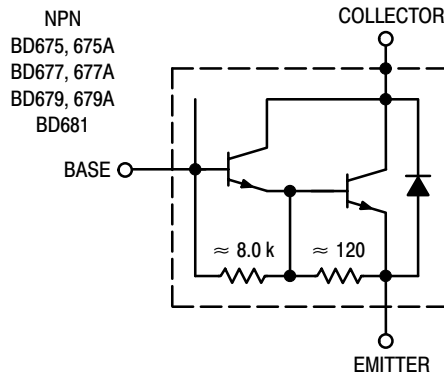
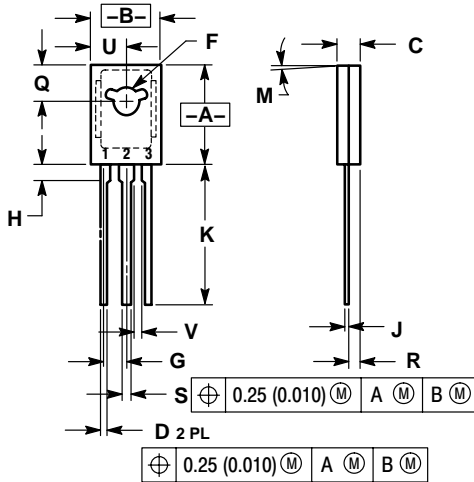


Figure 3. Darlington Circuit Schematic

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PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:

- PIN 1. EMITTER
- COLLECTOR
- BASE

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